

TO-92S Plastic-Encapsulate Transistors

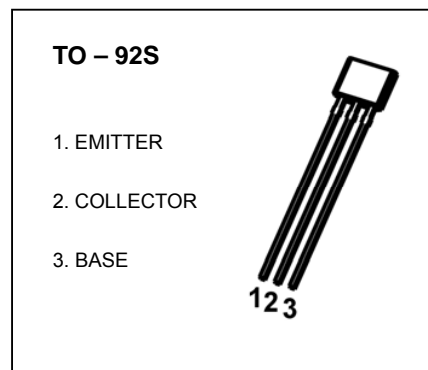
2SC536S TRANSISTOR (NPN)

FEATURES

- General Purpose Switching Application

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	100	mA
P _C	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	417	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =35V, I _E =0			1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			1	μA
DC current gain	h _{FE}	V _{CE} =6V, I _C =1mA	60		960	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA			0.5	V
Collector output capacitance	C _{ob}	V _{CB} =6V, I _E =0, f=1MHz		3.5		pF
Transition frequency	f _T	V _{CE} =6V, I _C =1mA, f=100MHz		100		MHz

CLASSIFICATION OF h_{FE}

RANK	D	E	F	G	H
RANGE	60-120	100-200	160-320	280-560	480-960